

Design and Modeling of a 0.4mW/Ch Multi-Channel Integrated Circuit for Infrared Gas Recognition

S. Sutula, C. Ferrer and F. Serra-Graells

stepan.sutula@imb-cnm.csic.es

Integrated Circuits and Systems (ICAS)
Instituto de Microelectrónica de Barcelona, IMB-CNM(CSIC)

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- 1 Introduction
- 2 ROIC Channel Architecture
- 3 Pre-Amplification and Filtering
- 4 Blind Cancellation and Lock-in Demodulation
- 5 Integrating A/D Conversion
- 6 Post Layout High Level Modeling
- 7 CMOS Integration and Experimental Results
- 8 Conclusions

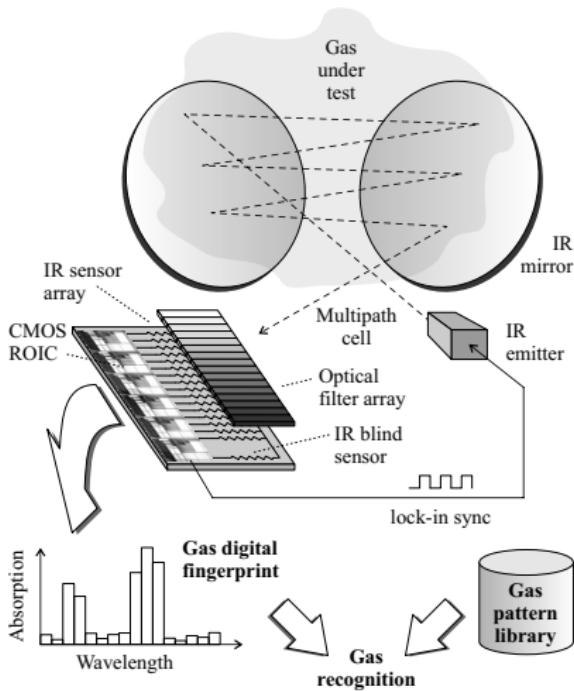


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Introduction

- ▶ Real-time **gas recognition** for environmental monitoring, toxic gas detection...
- ▶ **IR spectroscopic absorption digital fingerprint**
- ▶ Thermal μ bolometer LWIR sensing array
- ▲ Multi-channel ROIC for fast acquisition and low-noise
- ▲ Channel **lock-in** demodulation for high-accuracy
- ▲ Low-power operation to avoid thermal drifts of IR sensors
- ▲ **Compact pitch** for direct sensors-ROIC bonding



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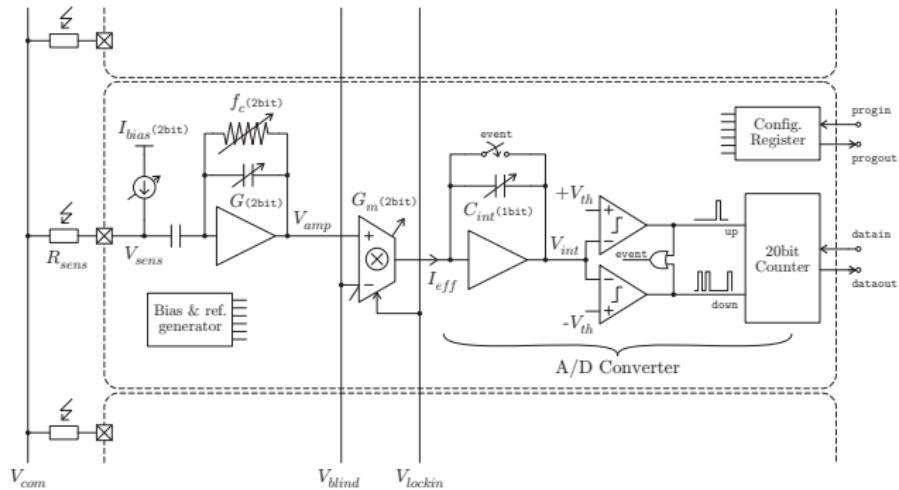
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ROIC Channel Architecture



- ▲ High programmability
- ▲ No external components
- ▲ Built-in bias generators for low crosstalk
- ▲ Digital only interface

- ▶ External **lock-in synchronization**
- ▶ Dedicated **blind channel** for cancellation of common disturbing signals
- ▶ Individual **configuration** register per channel

$$\Delta V_{sens} = I_{bias} \Delta R_{sens}$$

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Pre-Amplification and Filtering

- ▼ Sub-Hz high-pass specs
 - ▼ Independent gain and corner programmability required

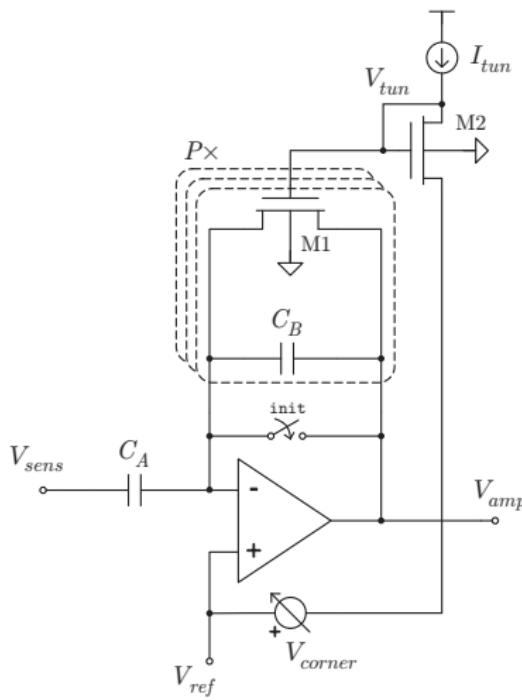
▲ Highly linear cap amplifier:

$$G = \frac{\Delta V_{amp}}{\Delta V_{sens}} = \frac{C_A}{C_B}$$

▲ **Subthreshold** MRC filtering:

$$f_c = f_{co} e^{-\frac{V_{corner}}{U_t}} \quad f_{co} = \frac{1}{2\pi} \frac{I_{tun(PTAT)}}{C_B U_t}$$

▲ **Fast initialization** switch



Pre-Amplification and Filtering

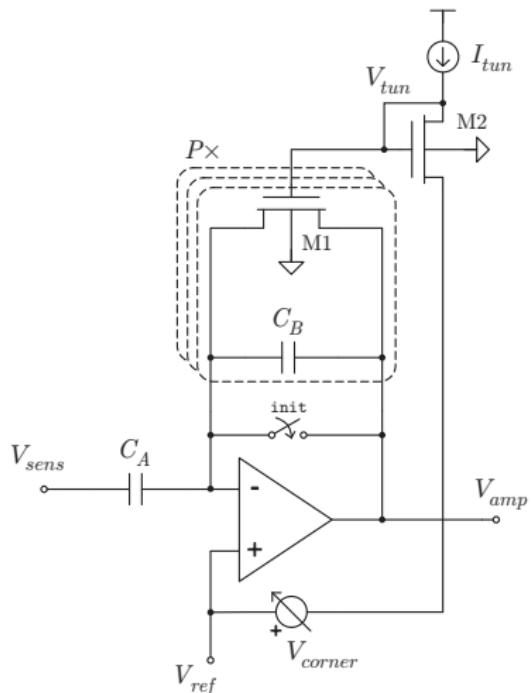
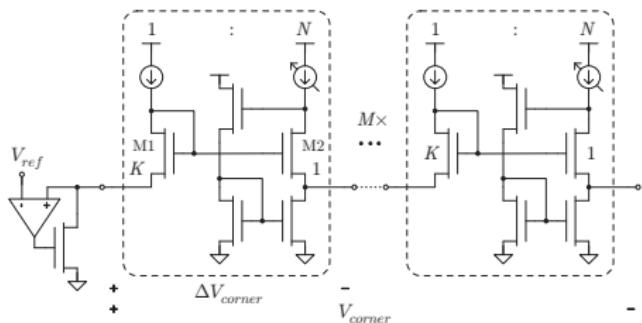
▲ Gain tuning by P scaling

▲ Multi-decade filter log tuning:

$$V_{corner} = M \Delta V_{corner} = M U_t \ln(NK)$$

$$f_c = \frac{f_{co}}{(NK)^M}$$

$$f_c \times 10^{\pm 3} \Leftrightarrow V_{corner} \pm 173\text{mV} \text{ at } 25^\circ\text{C}$$



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Blind Cancellation and Lock-in Demodulation

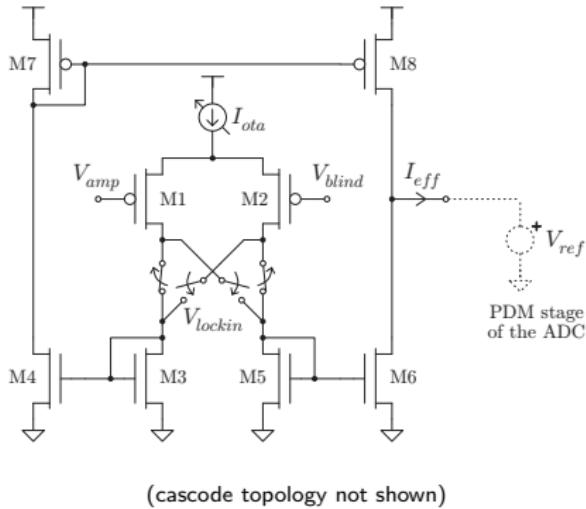
- ▶ Differential to **single ended**
- ▶ Voltage-to-**current** conversion
- ▶ **Lock-in** demodulation

- ▲ Low-power subthreshold OTA:

$$G_m = \frac{I_{eff}}{\Delta V_{amp}} = \frac{I_{ota}}{2nU_t} \propto U_t$$

$$I_{ota} \propto I_S = 2n\beta U_t^2$$

- ▲ **Current-domain** lock-in demodulation by cross-coupling
- ▲ Voltage log compression allows **fast switching** at low-power

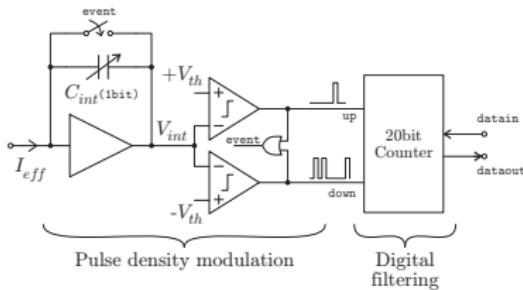


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Integrating A/D Conversion

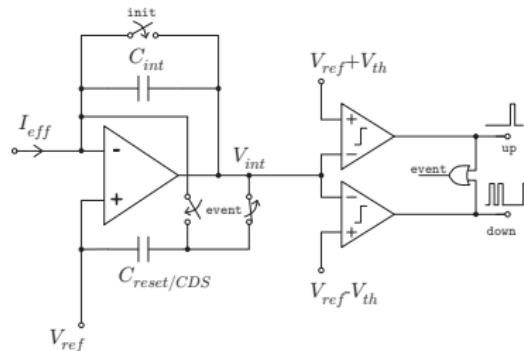
- ▶ **PDM noise shaping**
- ▶ **Digital counter** as low-pass filter
- ▶ **Asynchronous operation** for very low-power and low-crosstalk



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- ▶ **Asynchronous** operation for very low-power and low-crosstalk
- ▶ **Loss-less** analog integrator with **CDS** for high-linearity and noise reduction:

$$f_{PDM} = \frac{I_{eff}}{C_{int} V_{th}}$$



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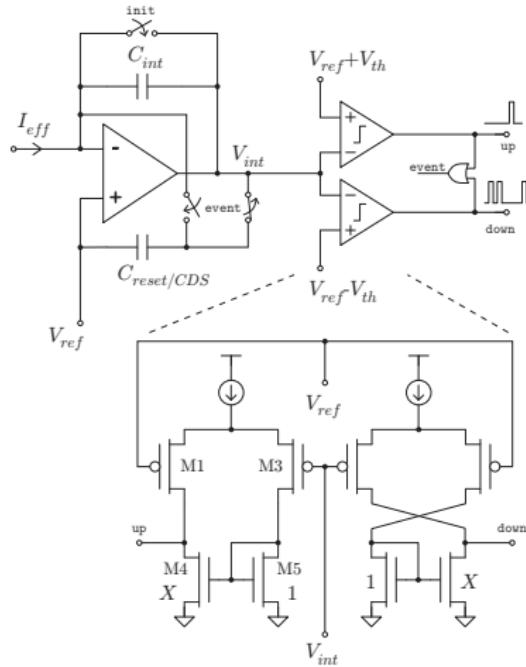
$$f_{PDM} = \frac{I_{eff}}{C_{int} V_{th}}$$

- ▶ **Built-in threshold comparator:**

$$V_{th} = n U_t \ln X$$

- ▶ **Thermal compensation** of G_m :

$$q_{adc} = \lfloor n_{adc} \rfloor \quad n_{adc} = T_{samp} f_{PDM} = \frac{C_A}{C_B} \frac{G_m}{V_{th}} \frac{T_{samp}}{C_{int}} \Delta R_{sens}$$

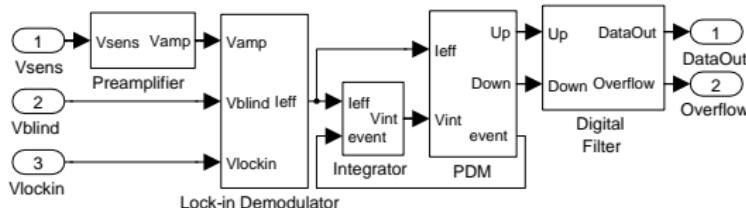


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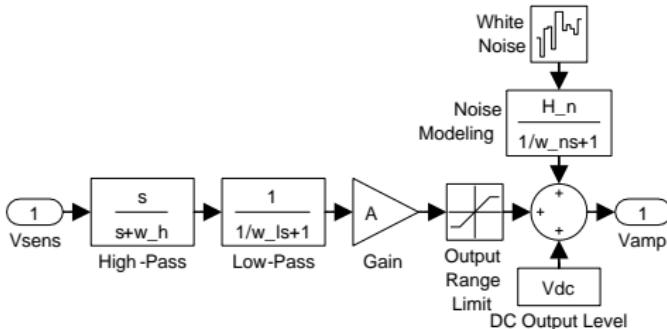
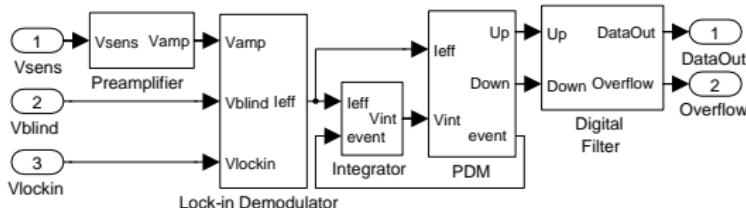
Post Layout High Level Modeling

- ▲ Simulation time reduction
- ▲ Complete read-out channel model
- ▲ Entire set of channel configurations



Post Layout High Level Modeling

- ▲ Simulation time reduction
- ▲ Complete read-out channel model
- ▲ Entire set of channel configurations
- ▲ Wide range of nonidealities modeling
- ▶ Technology process and temperature
- ▶ Flicker and thermal noise options
- ▶ External sensor modeling



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CMOS Integration and Experimental Results

- ▶ 0.35 μ m 2P4M CMOS channel module **test chip**
- ▶ Main **design parameters**:

$$C_A = 20\text{pF}$$

$$C_B = \{0.1, 0.2, 0.4, 1\}\text{pF}$$

$$K = 10$$

$$N = \{1, 11\}$$

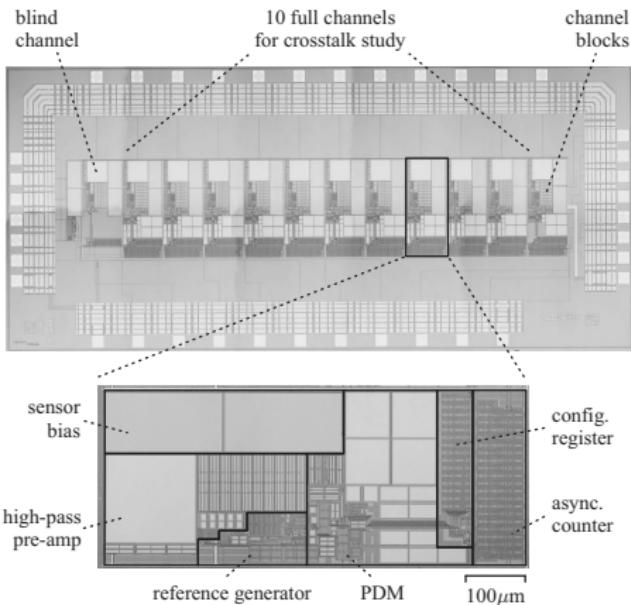
$$M = 3$$

$$I_{tun} = 100\text{nA}$$

$$I_{ota} = \{1, 2, 5, 10\}\mu\text{A}$$

$$V_{th} = 120\text{mV}$$

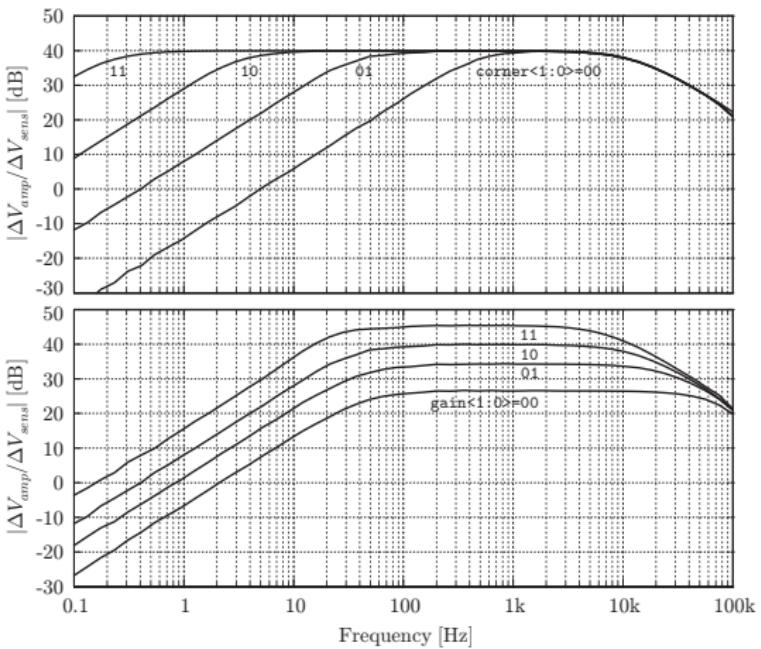
$$T_{pulse} = 500\text{ns}$$



▲ Access to intermediate stages

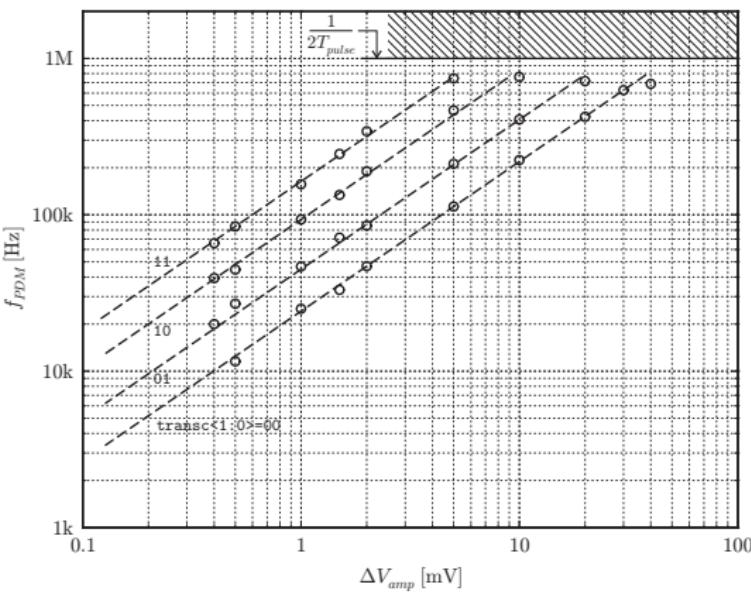
CMOS Integration and Experimental Results

- ▲ Sub-Hz pre-amplifier independent tuning (16 configurations)



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- ▲ Highly linear PDM up to pulse width hard limit



for cint<0>=0

CMOS Integration and Experimental Results

- ▲ Sub-Hz pre-amplifier independent tuning (16 configurations)
 - ▲ Highly linear PDM up to pulse width hard limit
 - ▲ 9bit digital programmability per channel
 - ▲ No crosstalk observed between channels
- experimental (vs simulated) results per channel

Parameter	Value	Units
I_{bias} bias<1:0>=00	0.97 (1)	μA
01	1.9 (2)	
10	4.6 (5)	
11	9.1 (10)	
f_c corner<1:0>=00	0.3 (0.25)	Hz
01	3.9 (4.1)	
10	50 (60)	
11	625 (825)	
G gain<1:0>=00	27 (26)	dB
01	34 (34)	
10	40 (40)	
11	46 (45)	
G_m transc<1:0>=00	(15)	μS
01	(30)	
10	(70)	
11	(130)	
C_{int} cint<0>=0	(5)	pF
1	(10)	pF
Total Harmonic Distortion	<0.25	%
Crosstalk	<0.5	LSB
V_{nied} for $R_{sens}=300\text{k}\Omega$	(100)	$\text{nV}_{\text{rms}}/\sqrt{\text{Hz}}$
Supply voltage	3.3	V
Supply current	100	μA
Silicon area	300×715	μm^2

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Conclusions

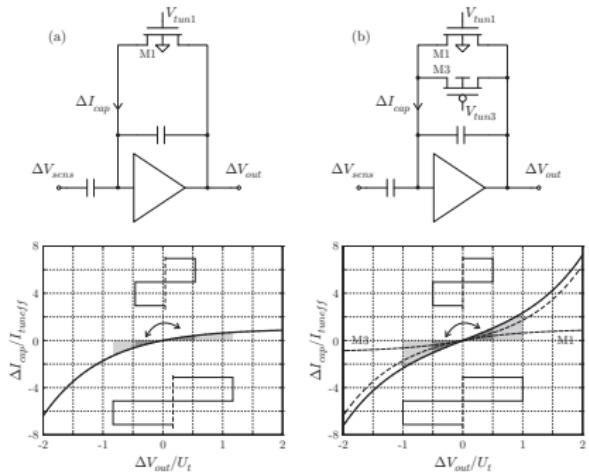
- ▶ **Digital read-out** channel for IR spectroscopic gas recognition
- ▶ **Fully integrable** sub-Hz high-pass pre-amplification
- ▶ **Blind** cancellation and **lock-in** demodulation
- ▶ **Highly linear** integrating A/D conversion
- ▶ **High-programmability** (9bit) per channel
- ▶ **Low-current** ($100\mu\text{A}$) and **compact** (0.2mm^2) channel module in $0.35\mu\text{m}$ 2P4M CMOS technology
- ▶ Experimental results **agree** with simulated performance
- ▶ Post layout **high level modeling**
- ▶ **No-crosstalk** reported between channels

... thanks for your attention!

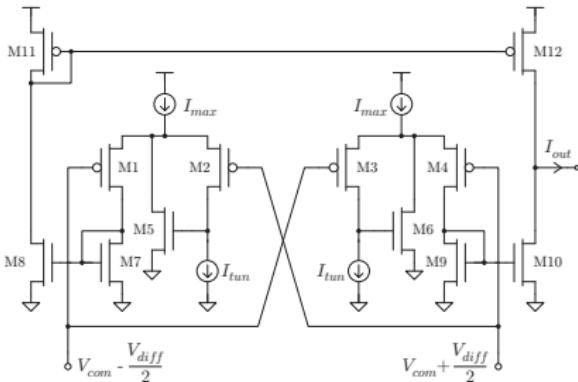


Improvements?

▼ Pre-amplifier dynamic offset



▼ OTA linear range



▲ A 32-channel ROIC is under development!